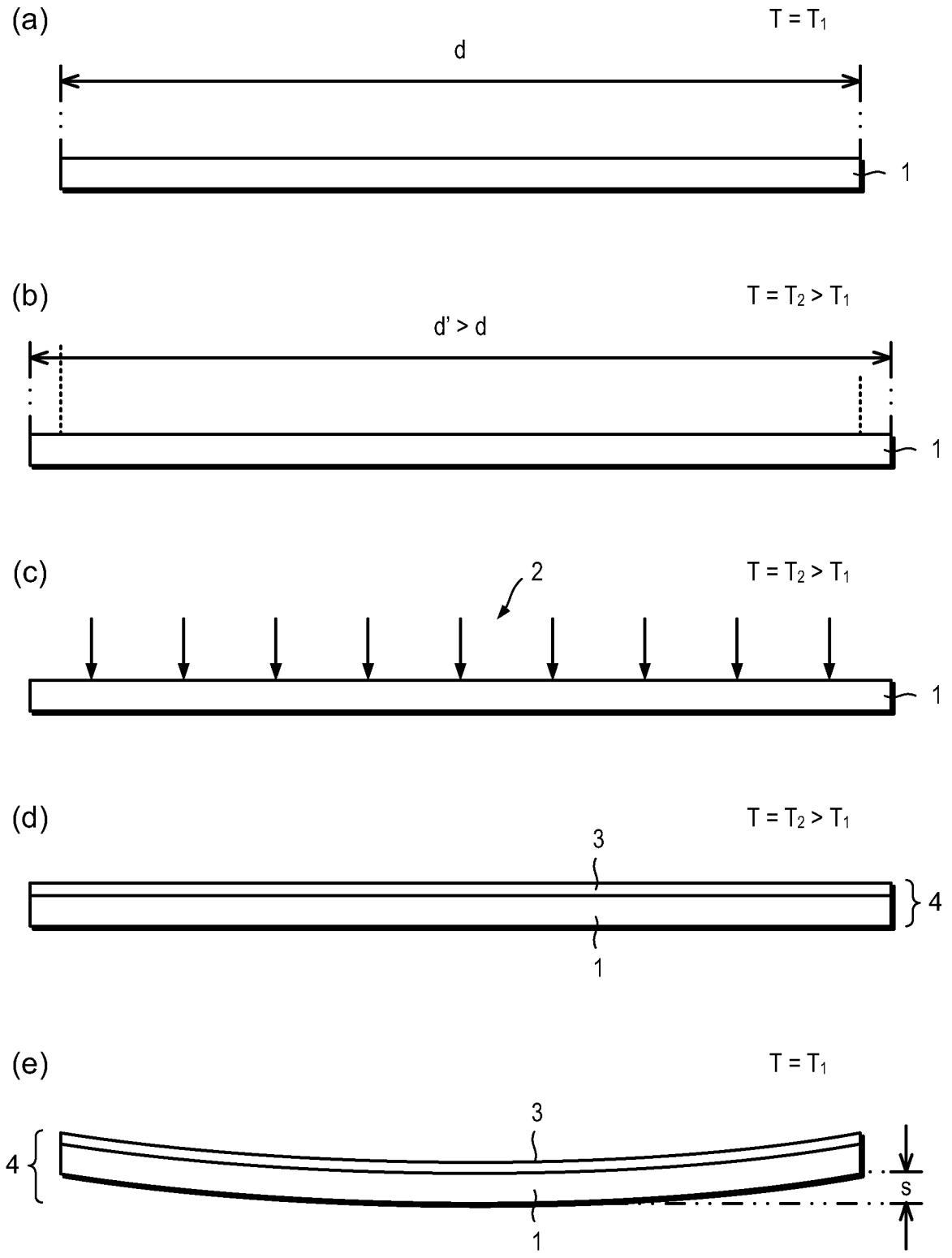


Fig. 1

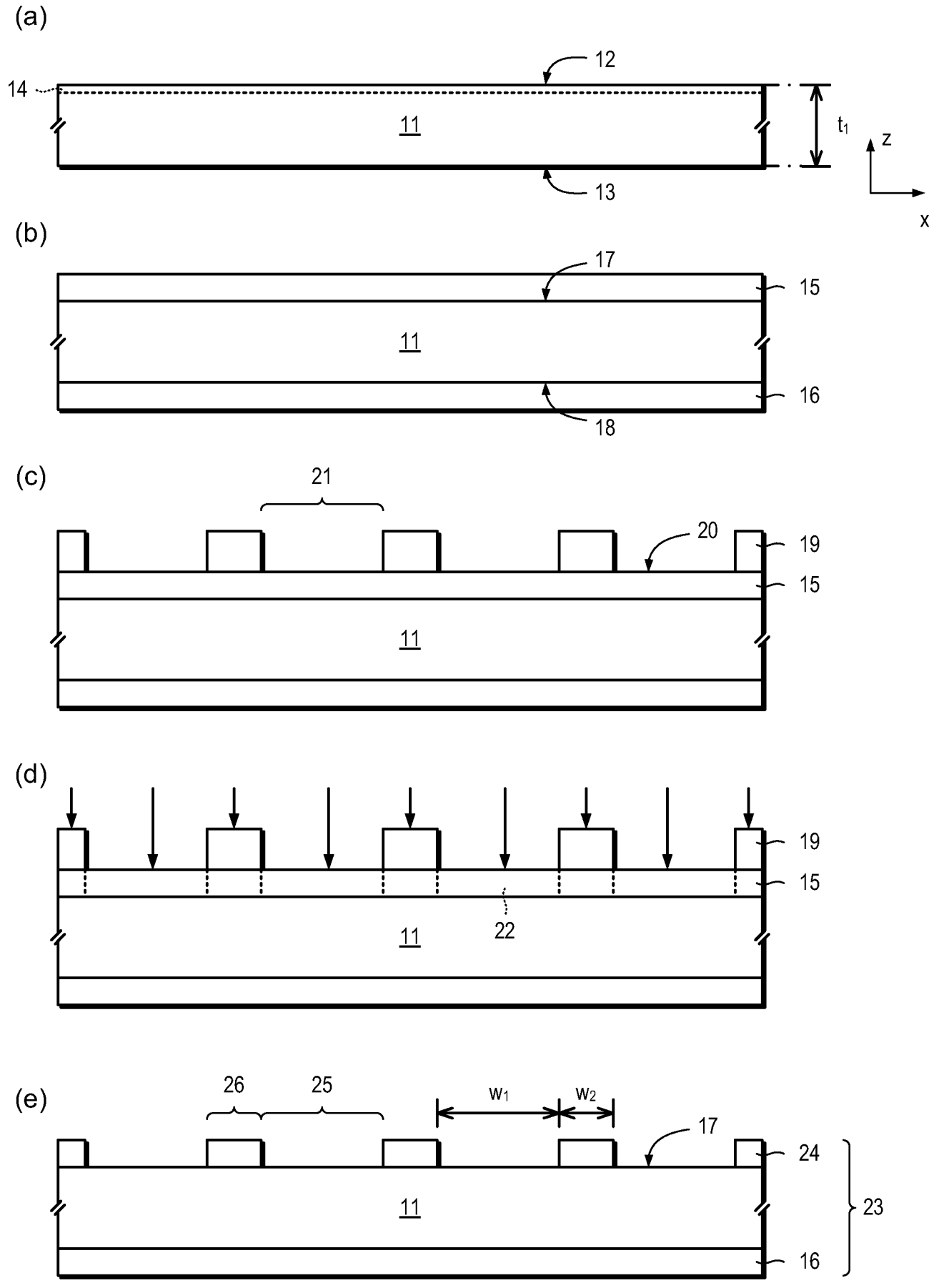

(a)
12
14
11
t_1
z
13
x
(b)
17
15
11
16
18
(c)
21
20
19
15
11
(d)
19
15
22
11
(e)
26
25
w_1
w_2
17
24
23
11
16

Fig. 2

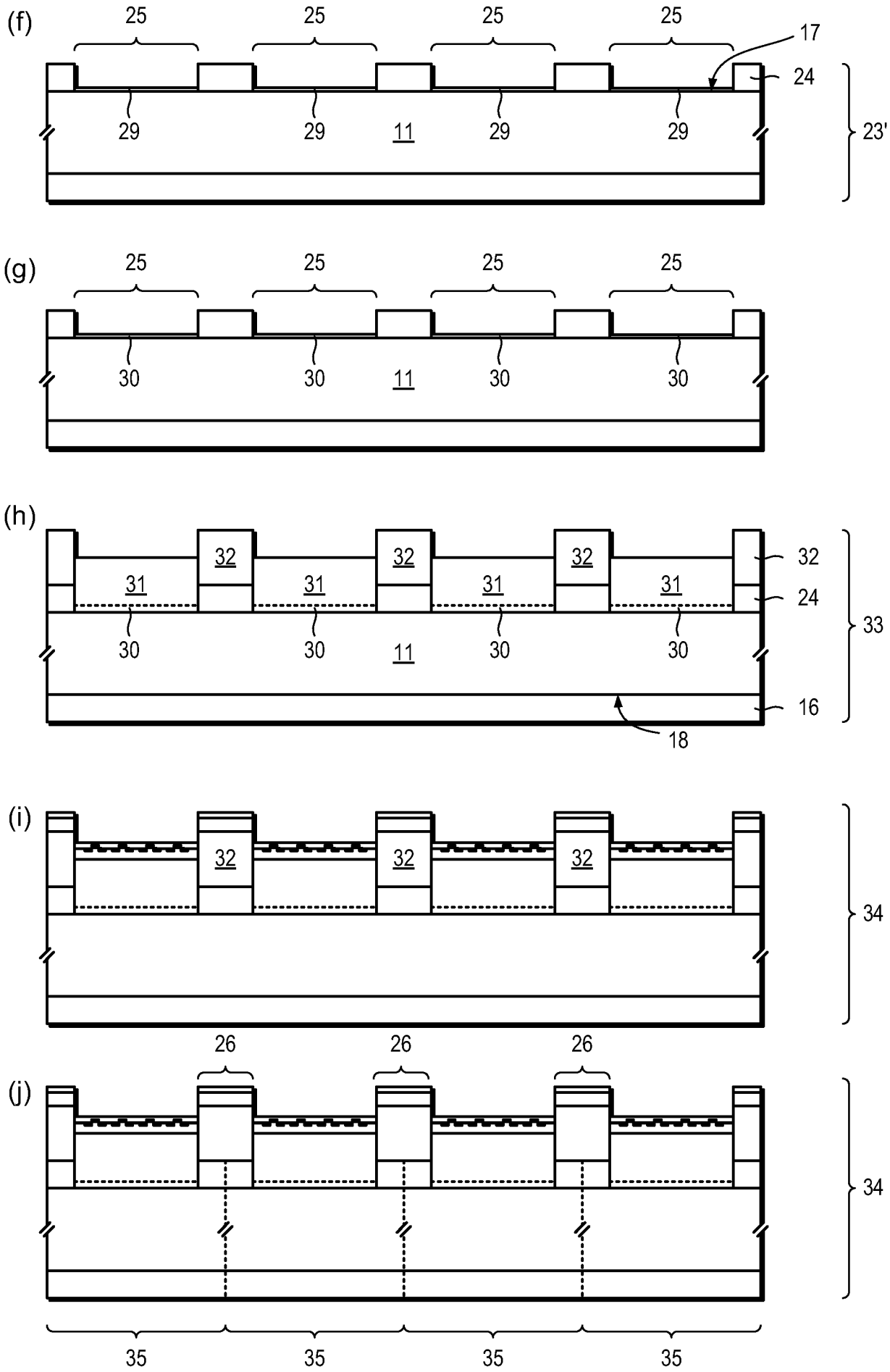

(f)
25
25
25
25
17
24
29
29
11
29
29
23'
(g)
25
25
25
25
30
30
11
30
30
(h)
32
32
32
32
31
31
31
31
30
30
11
30
30
33
16
18
(i)
32
32
32
34
26
26
26
(j)
34
35
35
35
35

Fig. 2

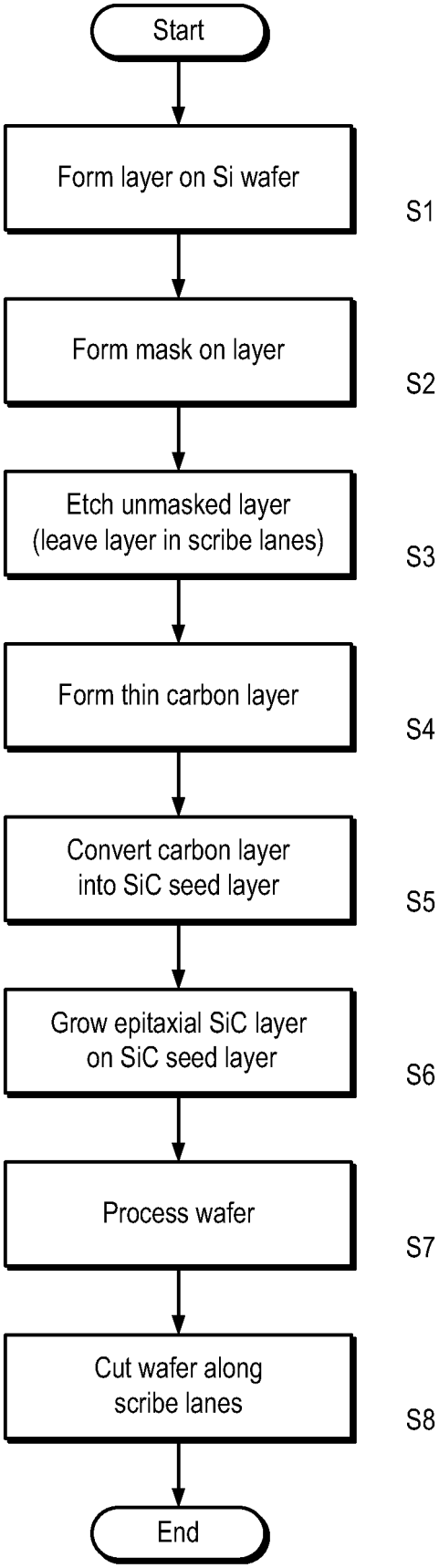

Start
Form layer on Si wafer
S1
Form mask on layer
S2
Etch unmasked layer
(leave layer in scribe lanes)
S3
Form thin carbon layer
S4
Convert carbon layer
into SiC seed layer
S5
Grow epitaxial SiC layer
on SiC seed layer
S6
Process wafer
S7
Cut wafer along
scribe lanes
S8
End

Fig. 3

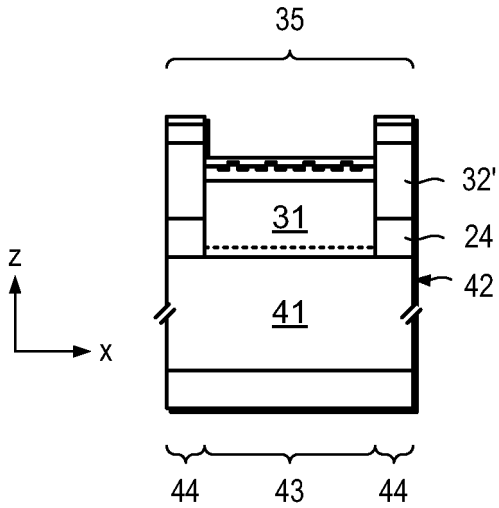


Fig. 4a

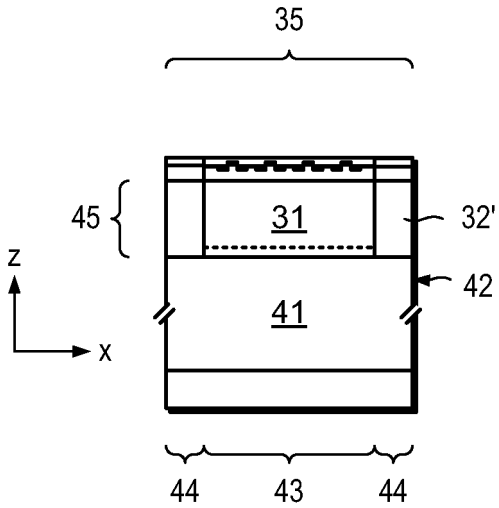


Fig. 4b

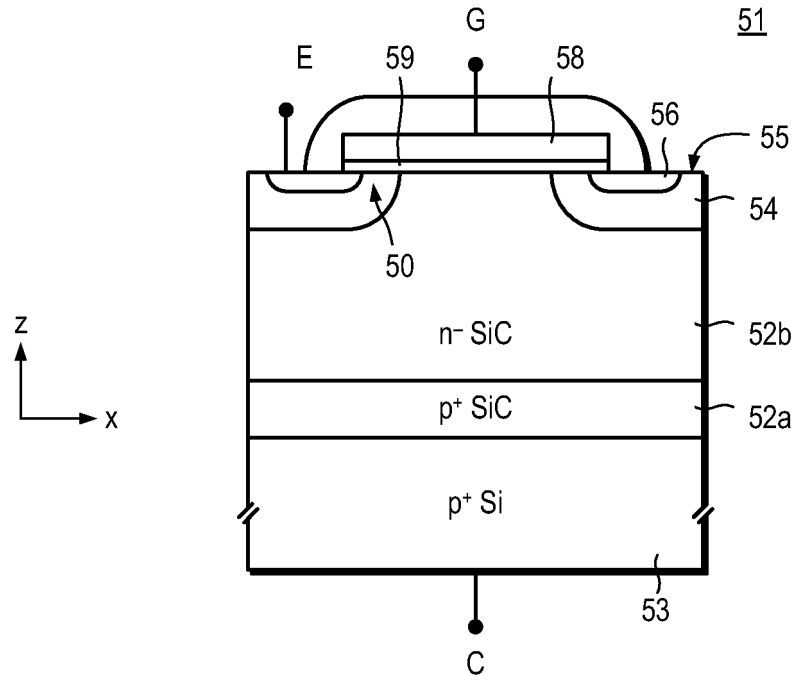


Fig. 5